



QUAD/DUAL SUPERCAPACITOR AUTO BALANCING (SAB™) MOSFET ARRAY

GENERAL DESCRIPTION

The ALD810017/ALD910017 are members of the ALD8100xx (quad) and ALD9100xx (dual) family of Supercapacitor Auto Balancing MOSFETs, or SAB™ MOSFETs. SAB MOSFETs are built with production proven EPAD® technology and are designed to address voltage and leakage-current balancing of supercapacitors connected in series. Supercapacitors, also known as ultracapacitors or supercaps, connected in series can be leakage-current balanced by using a combination of one or more devices connected across each supercapacitor stack to prevent over-voltages.

The ALD810017 offers a set of unique, precise operating voltage and current characteristics for each of four SAB MOSFET devices, as shown in its Operating Electrical Characteristics table. It can be used to balance up to four supercapacitors connected in series. The ALD910017 has its own set of unique precision Operating Electrical Characteristics for each of its two SAB MOSFET devices, suitable for up to two series-connected supercapacitors.

Each SAB MOSFET features a precision gate threshold voltage in the V_t mode, which is 1.70V when the gate-drain source terminals ($V_{GS} = V_{DS}$) are connected together at a drain-source current of $I_{DS(ON)} = 1\mu A$. In this mode, input voltage $V_{IN} = V_{GS} = V_{DS}$. Different V_{IN} produces an Output Current $I_{OUT} = I_{DS(ON)}$ characteristic and results in an effective variable resistor that varies in value exponentially with V_{IN} . This V_{IN} , when connected across each supercapacitor in a series, balances each supercapacitor to within its voltage and current limits.

When $V_{IN} = 1.70V$ is applied to an ALD810017/ALD910017, its I_{OUT} is $1\mu A$. For a 100mV increase in V_{IN} , to 1.80V, I_{OUT} increases by about tenfold. For an additional increase in V_{IN} to 1.92V for the ALD910017 (1.94V for the ALD810017), I_{OUT} increases one hundredfold, to $100\mu A$. Conversely, for a 100mV decrease in V_{IN} to 1.60V, I_{OUT} decreases to one tenth of its previous value, to $0.1\mu A$. Another 100mV decrease in input voltage would reduce I_{OUT} to $0.01\mu A$. Hence, when an ALD810017/ALD910017 SAB MOSFET is connected across a supercapacitor that charges to less than 1.50V, it would dissipate essentially no power.

(Continued on next page)

PRODUCT FAMILY SPECIFICATIONS

For more information on supercapacitor balancing, how SAB MOSFETs achieve automatic supercapacitor balancing, the device characteristics of the SAB MOSFET family, product family product selection guide, applications, configurations, and package information, please download from www.aldinc.com the document:

"ALD8100xx/ALD9100xx Family of Supercapacitor Auto Balancing (SAB™) MOSFET ARRAYS"

ORDERING INFORMATION ("L" suffix denotes lead-free (RoHS))

Package	Operating Temperature Range	
	0°C to +70°C (Commercial)	-40°C to +85°C (Industrial)
16-Pin SOIC	ALD810017SCL	ALD810017SCLI
8-Pin SOIC	ALD910017SAL	ALD910017SALI

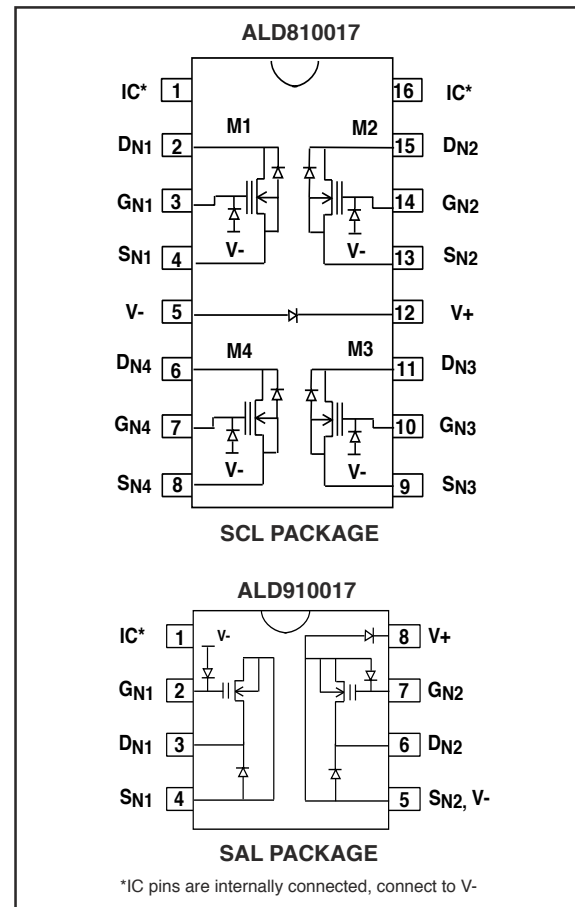
FEATURES & BENEFITS

- Simple and economical to use
- Precision factory trimmed
- Automatically regulates and balances leakage currents
- Effective for supercapacitor charge-balancing
- Balances up to 4 supercaps with a single IC package
- Balances 2-cell, 3-cell, 4-cell series-connected supercaps
- Scalable to larger supercap stacks and arrays
- Near zero additional leakage currents
- Zero leakage at 0.3V below rated voltages
- Balances series and/or parallel-connected supercaps
- Leakage currents are exponential function of cell voltages
- Active current ranges from $<0.3nA$ to $>1000\mu A$
- Always active, always fast response time
- Minimizes leakage currents and power dissipation

APPLICATIONS

- Series-connected supercapacitor cell leakage balancing
- Energy harvesting
- Long term backup battery with supercapacitor outputs
- Zero-power voltage divider at selected voltages
- Matched current mirrors and current sources
- Zero-power mode maximum voltage limiter
- Scaled supercapacitor stacks and arrays

PIN CONFIGURATIONS



ABSOLUTE MAXIMUM RATINGS

V+ to V- voltage	15.0V
Drain-Source voltage, V_{DS}	10.6V
Gate-Source voltage, V_{GS}	10.6V
Operating Current	80mA
Power dissipation	500mW
Operating temperature range SCL	0°C to +70°C
Operating temperature range SCL1	-40°C to +85°C
Storage temperature range	-65°C to +150°C
Lead temperature, 10 seconds	+260°C

CAUTION: ESD Sensitive Device. Use static control procedures in ESD controlled environment.

OPERATING ELECTRICAL CHARACTERISTICS

V+ = +5V, V- = GND, $T_A = 25^\circ\text{C}$, $V_{IN} = V_{GS} = V_{DS}$, $I_{OUT} = I_{DS(ON)}$ unless otherwise specified

Parameter	Symbol	ALD810017			Unit	Test Conditions
		Min	Typ	Max		
Gate Threshold Voltage	V_t	1.68	1.70	1.72	V	$V_{GS} = V_{DS}$; $I_{DS(ON)} = 1\mu\text{A}$
Offset Voltage	V_{OS}		5	20	mV	$V_{t1} - V_{t2}$ or $V_{t3} - V_{t4}$
Offset Voltage Tempco	TC_{VOS}		5		$\mu\text{V}/\text{C}$	$V_{t1} - V_{t2}$ or $V_{t3} - V_{t4}$
Gate Threshold Voltage Tempco	TC_{V_t}		-2.2		mV/C	$V_{GS} = V_{DS}$; $I_{DS(ON)} = 1\mu\text{A}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		0.0001 13000		μA $\text{M}\Omega$	$V_{IN} = 1.30\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		0.001 1400		μA $\text{M}\Omega$	$V_{IN} = 1.40\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		0.01 150		μA $\text{M}\Omega$	$V_{IN} = 1.50\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		0.1 16		μA $\text{M}\Omega$	$V_{IN} = 1.60\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		1 1.7		μA $\text{M}\Omega$	$V_{IN} = 1.70\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		10 0.18		μA $\text{M}\Omega$	$V_{IN} = 1.80\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		100 0.019		μA $\text{M}\Omega$	$V_{IN} = 1.94\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		300 0.007		μA $\text{M}\Omega$	$V_{IN} = 2.04\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		1000 0.002		μA $\text{M}\Omega$	$V_{IN} = 2.22\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		3000 0.001		μA $\text{M}\Omega$	$V_{IN} = 2.52\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		10000 0.0003		μA $\text{M}\Omega$	$V_{IN} = 3.12\text{V}$
Drain Source Breakdown Voltage	BV_{DSX}	10.6			V	
Drain Source Leakage Current ¹	$I_{DS(OFF)}$		10	400	pA nA	$V_{IN} = V_{GS} = V_{DS} = V_t - 1.0$ $V_{IN} = V_{GS} = V_{DS} = V_t - 1.0$, $T_A = +125^\circ\text{C}$
Gate Leakage Current ¹	I_{GSS}		5	200	pA nA	$V_{GS} = 5.0\text{V}$, $V_{DS} = 0\text{V}$ $V_{GS} = 5.0\text{V}$, $V_{DS} = 0\text{V}$, $T_A = +125^\circ\text{C}$
Input Capacitance	C_{ISS}		15		pF	$V_{GS} = 0\text{V}$, $V_{DS} = 5.0\text{V}$
Turn-on Delay Time	t_{on}		10		ns	
Turn-off Delay Time	t_{off}		10		ns	
Crosstalk			60		dB	$f = 100\text{KHz}$

ABSOLUTE MAXIMUM RATINGS

V+ to V- voltage	15.0V
Drain-Source voltage, V_{DS}	10.6V
Gate-Source voltage, V_{GS}	10.6V
Operating Current	80mA
Power dissipation	500mW
Operating temperature range SAL	0°C to +70°C
Operating temperature range SALI	-40°C to +85°C
Storage temperature range	-65°C to +150°C
Lead temperature, 10 seconds	+260°C

CAUTION: ESD Sensitive Device. Use static control procedures in ESD controlled environment.

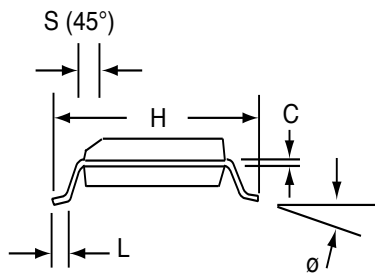
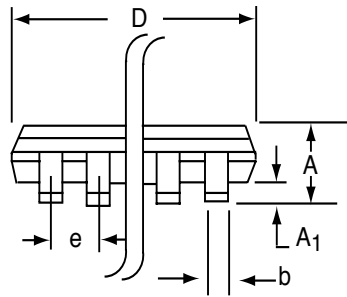
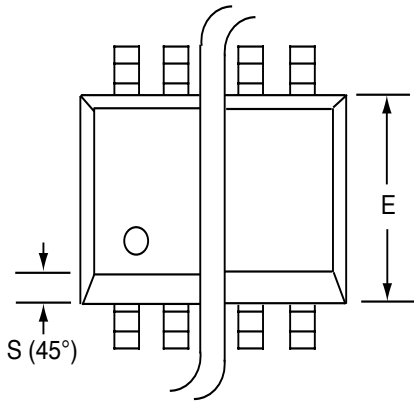
OPERATING ELECTRICAL CHARACTERISTICS

V+ = +5V, V- = GND, $T_A = 25^\circ\text{C}$, $V_{IN} = V_{GS} = V_{DS}$, $I_{OUT} = I_{DS(ON)}$ unless otherwise specified

Parameter	Symbol	ALD910017			Unit	Test Conditions
		Min	Typ	Max		
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Offset Voltage	V_{OS}		5	20	mV	$V_{t1} - V_{t2}$
Offset Voltage Tempco	TC_{VOS}		5		$\mu\text{V}/\text{C}$	$V_{t1} - V_{t2}$
Gate Threshold Voltage Tempco	TC_{V_t}		-2.2		mV/C	$V_{GS} = V_{DS}$; $I_{DS(ON)} = 1\mu\text{A}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		0.0001 13000		μA $\text{M}\Omega$	$V_{IN} = 1.30\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		0.001 1400		μA $\text{M}\Omega$	$V_{IN} = 1.40\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		0.01 150		μA $\text{M}\Omega$	$V_{IN} = 1.50\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		0.1 16		μA $\text{M}\Omega$	$V_{IN} = 1.60\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		1 1.7		μA $\text{M}\Omega$	$V_{IN} = 1.70\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		10 0.18		μA $\text{M}\Omega$	$V_{IN} = 1.80\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		100 0.019		μA $\text{M}\Omega$	$V_{IN} = 1.92\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		300 0.007		μA $\text{M}\Omega$	$V_{IN} = 2.00\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		1000 0.002		μA $\text{M}\Omega$	$V_{IN} = 2.14\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		3000 0.001		μA $\text{M}\Omega$	$V_{IN} = 2.20\text{V}$
Output Current Drain Source On Resistance	I_{OUT} $R_{DS(ON)}$		10000 0.0003		μA $\text{M}\Omega$	$V_{IN} = 2.70\text{V}$
Drain Source Breakdown Voltage	BV_{DSX}	10.6			V	
Drain Source Leakage Current ¹	$I_{DS(OFF)}$		10	400	pA nA	$V_{IN} = V_{GS} = V_{DS} = V_t - 1.0$ $V_{IN} = V_{GS} = V_{DS} = V_t - 1.0$, $T_A = +125^\circ\text{C}$
Gate Leakage Current ¹	I_{GSS}		5	200	pA nA	$V_{GS} = 5.0\text{V}$, $V_{DS} = 0\text{V}$ $V_{GS} = 5.0\text{V}$, $V_{DS} = 0\text{V}$, $T_A = +125^\circ\text{C}$
Input Capacitance	C_{ISS}		30		pF	$V_{GS} = 0\text{V}$, $V_{DS} = 5.0\text{V}$
Turn-on Delay Time	t_{on}		10		ns	
Turn-off Delay Time	t_{off}		10		ns	
Crosstalk			60		dB	$f = 100\text{KHz}$

SOIC-16 PACKAGE DRAWING

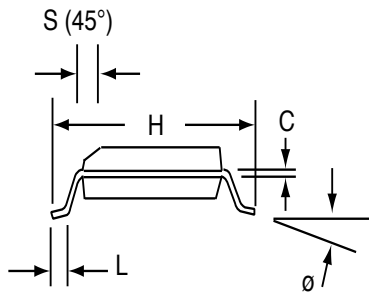
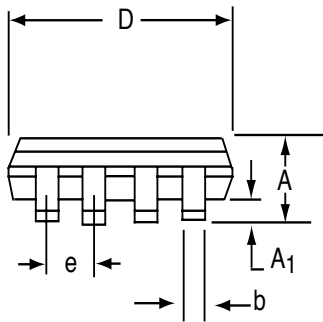
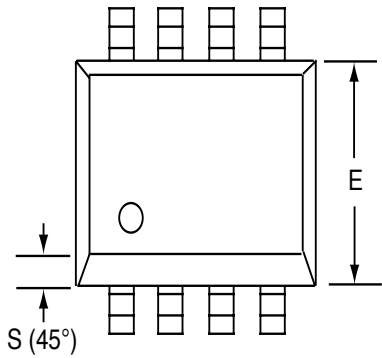
16 Pin Plastic SOIC Package



Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A₁	0.10	0.25	0.004	0.010
b	0.35	0.45	0.014	0.018
C	0.18	0.25	0.007	0.010
D-16	9.80	10.00	0.385	0.394
E	3.50	4.05	0.140	0.160
e	1.27 BSC		0.050 BSC	
H	5.70	6.30	0.224	0.248
L	0.60	0.937	0.024	0.037
∅	0°	8°	0°	8°
S	0.25	0.50	0.010	0.020

SOIC-8 PACKAGE DRAWING

8 Pin Plastic SOIC Package



Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A₁	0.10	0.25	0.004	0.010
b	0.35	0.45	0.014	0.018
C	0.18	0.25	0.007	0.010
D-8	4.69	5.00	0.185	0.196
E	3.50	4.05	0.140	0.160
e	1.27 BSC		0.050 BSC	
H	5.70	6.30	0.224	0.248
L	0.60	0.937	0.024	0.037
∅	0°	8°	0°	8°
S	0.25	0.50	0.010	0.020

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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